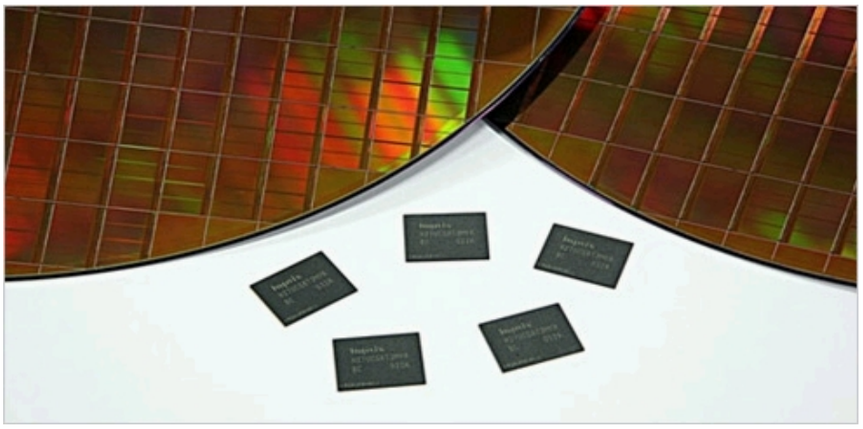
# Release of 26nm 32Gb High Speed MLC

## Product Information



Hynix has developed 32Gb MLC(Multi Level Cell) High Speed NAND Flash based on 26nm process technology, and is now validating the products on major controller makers.

This product supports both Legacy and high speed ONFI(Open NAND Flash Interface) 2.2 specification. It will be packaged in legacy 48TSOP(12x20mm) & 100FBGA(12x18mm).

With *DDR Mode, it can run 200MB/s high speed read/write operations with the 8 -bit bus. The product will find use in mobile applications such as smartphones, and media tablets but also in storage devices like USB 3.0 & *SSD, which will drive demand .

Hynix will start mass production from January 2011.

<note>
*DDR - Double Data Rate
**SSD - Solid State Drive

## Key Features

Multi Level Cell Technology
NAND Interface : x8 bus width
Supply voltage (3.3V device)
- Vcc = 2.7~3.6V, Vccq = 2.7~3.6V/1.7~1.95V
Organization : (8192+640) bytes x 256 pages x 2048 blocks
Open NAND Flash Interface(ONFI) 2.2 Compliant
- Supports MLC/SLC transition by command
- Asynchronous I/O performance(Sequential Access time : tRC/tWC = 16ns)
- Synchronous I/O performance(DDR, read/write throughput per pin : 200MB/s

## Product Lineup

| Part Number | Density | Technology | Interface Spec. | Package Type | Customer Sample |
|---|---|---|---|---|---|
| H27UBG8T2BTRBC | 32Gb | 26nm | Legacy | 48 TSOP (12x20x1.2mm) | Now |
| H27UBG8T2BIRBC | 32Gb | 26nm | ONFi2.2 (DDR) | 100 FBGA (12x18x1.4mm) | 11.01 |



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